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### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

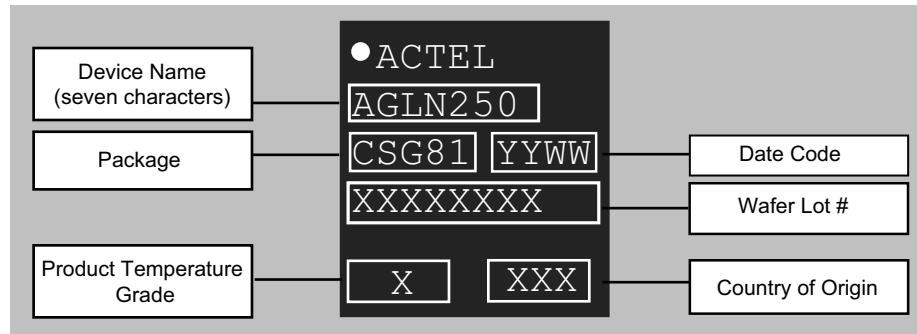
#### Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	1536
Total RAM Bits	18432
Number of I/O	71
Number of Gates	60000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/agln060v5-zvq100i">https://www.e-xfl.com/product-detail/microchip-technology/agln060v5-zvq100i</a>

## Device Marking

Microsemi normally topside marks the full ordering part number on each device. There are some exceptions to this, such as some of the Z feature grade nano devices, the V2 designator for IGLOO devices, and packages where space is physically limited. Packages that have limited characters available are UC36, UC81, CS81, QN48, QN68, and QFN132. On these specific packages, a subset of the device marking will be used that includes the required legal information and as much of the part number as allowed by character limitation of the device. In this case, devices will have a truncated device marking and may exclude the applications markings, such as the I designator for Industrial Devices or the ES designator for Engineering Samples.

Figure 1 shows an example of device marking based on the AGLN250V2-CSG81. The actual mark will vary by the device/package combination ordered.



**Figure 1 • Example of Device Marking for Small Form Factor Packages**

## IGLOO nano Products Available in the Z Feature Grade

IGLOO nano-Z Devices	AGLN030Z*	AGLN060Z*	AGLN125Z*	AGLN250Z*
<b>Packages</b>	QN48	–	–	–
	QN68	–	–	–
	UC81	–	–	–
	CS81	CS81	CS81	CS81
	VQ100	VQ100	VQ100	VQ100

Note: \*Not recommended for new designs.

## Temperature Grade Offerings

	AGLN010	AGLN015*	AGLN020		AGLN060	AGLN125	AGLN250
Package				AGLN030Z*	AGLN060Z*	AGLN125Z*	AGLN250Z*
UC36	C, I	–	–	–	–	–	–
QN48	C, I	–	–	C, I	–	–	–
QN68	–	C, I	C, I	C, I	–	–	–
UC81	–	–	C, I	C, I	–	–	–
CS81	–	–	C, I	C, I	C, I	C, I	C, I
VQ100	–	–	–	C, I	C, I	C, I	C, I

Note: \* Not recommended for new designs.

C = Enhanced Commercial temperature range: –20°C to +85°C junction temperature

I = Industrial temperature range: –40°C to +100°C junction temperature

Contact your local Microsemi representative for device availability: <http://www.microsemi.com/soc/contact/default.aspx>.

**Table 2-2 • Recommended Operating Conditions <sup>1</sup>**

Symbol	Parameter		Extended Commercial	Industrial	Units
T <sub>J</sub>	Junction temperature		–20 to + 85 <sup>2</sup>	–40 to +100 <sup>2</sup>	°C
VCC	1.5 V DC core supply voltage <sup>3</sup>		1.425 to 1.575	1.425 to 1.575	V
	1.2 V–1.5 V wide range core voltage <sup>4,5</sup>		1.14 to 1.575	1.14 to 1.575	V
VJTAG	JTAG DC voltage		1.4 to 3.6	1.4 to 3.6	V
VPUMP <sup>6</sup>	Programming voltage	Programming mode	3.15 to 3.45	3.15 to 3.45	V
		Operation	0 to 3.6	0 to 3.6	V
VCCPLL <sup>7</sup>	Analog power supply (PLL)	1.5 V DC core supply voltage <sup>3</sup>	1.425 to 1.575	1.425 to 1.575	V
		1.2 V–1.5 V wide range core supply voltage <sup>4</sup>	1.14 to 1.575	1.14 to 1.575	V
VCCI and VMV <sup>8,9</sup>	1.2 V DC supply voltage <sup>4</sup>		1.14 to 1.26	1.14 to 1.26	V
	1.2 V DC wide range supply voltage <sup>4</sup>		1.14 to 1.575	1.14 to 1.575	V
	1.5 V DC supply voltage		1.425 to 1.575	1.425 to 1.575	V
	1.8 V DC supply voltage		1.7 to 1.9	1.7 to 1.9	V
	2.5 V DC supply voltage		2.3 to 2.7	2.3 to 2.7	V
	3.3 V DC supply voltage		3.0 to 3.6	3.0 to 3.6	V
	3.3 V DC wide range supply voltage <sup>10</sup>		2.7 to 3.6	2.7 to 3.6	V

**Notes:**

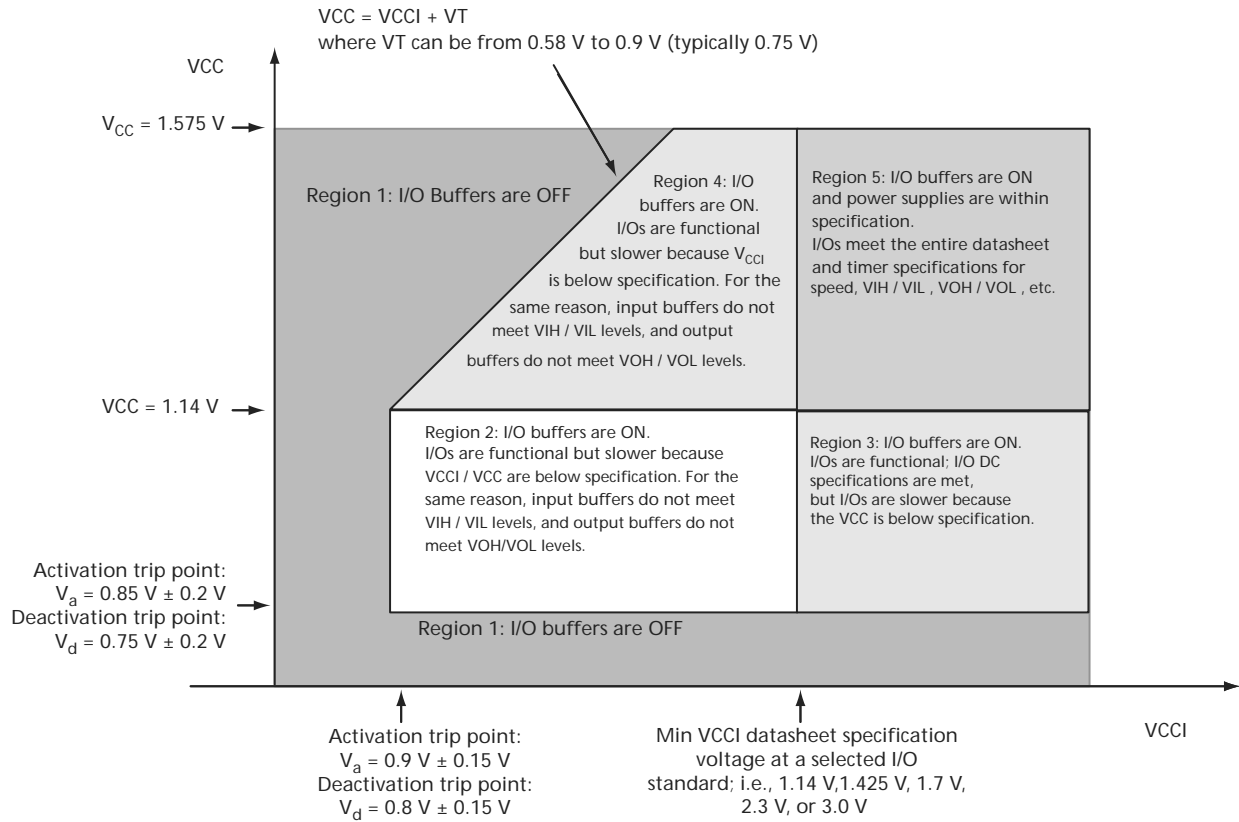
1. All parameters representing voltages are measured with respect to GND unless otherwise specified.
2. Default Junction Temperature Range in the Libero SoC software is set to 0°C to +70°C for commercial, and –40°C to +85°C for industrial. To ensure targeted reliability standards are met across the full range of junction temperatures, Microsemi recommends using custom settings for temperature range before running timing and power analysis tools. For more information regarding custom settings, refer to the New Project Dialog Box in the Libero Online Help.
3. For IGLOO® nano V5 devices
4. For IGLOO nano V2 devices only, operating at VCCI ≥ VCC
5. IGLOO nano V5 devices can be programmed with the VCC core voltage at 1.5 V only. IGLOO nano V2 devices can be programmed with the VCC core voltage at 1.2 V (with FlashPro4 only) or 1.5 V. If you are using FlashPro3 and want to do in-system programming using 1.2 V, please contact the factory.
6. V<sub>PUMP</sub> can be left floating during operation (not programming mode).
7. VCCPLL pins should be tied to VCC pins. See the "Pin Descriptions" chapter for further information.
8. VMV pins must be connected to the corresponding VCCI pins. See the Pin Descriptions chapter of the IGLOO nano FPGA Fabric User's Guide for further information.
9. The ranges given here are for power supplies only. The recommended input voltage ranges specific to each I/O standard are given in Table 2-21 on page 2-19. VCCI should be at the same voltage within a given I/O bank.
10. 3.3 V wide range is compliant to the JESD8-B specification and supports 3.0 V VCCI operation.

**Table 2-3 • Flash Programming Limits – Retention, Storage, and Operating Temperature<sup>1</sup>**

Product Grade	Programming Cycles	Program Retention (biased/unbiased)	Maximum Storage Temperature T <sub>STG</sub> (°C) <sup>2</sup>	Maximum Operating Junction Temperature T <sub>J</sub> (°C) <sup>2</sup>
Commercial	500	20 years	110	100
Industrial	500	20 years	110	100

**Notes:**

1. This is a stress rating only; functional operation at any condition other than those indicated is not implied.
2. These limits apply for program/data retention only. Refer to Table 2-1 on page 2-1 and Table 2-2 for device operating conditions and absolute limits.



**Figure 2-2 • V2 Devices – I/O State as a Function of  $V_{CCI}$  and  $V_{CC}$  Voltage Levels**

**Table 2-17 • Different Components Contributing to Dynamic Power Consumption in IGLOO nano Devices  
For IGLOO nano V2 Devices, 1.2 V Core Supply Voltage**

Parameter	Definition	Device-Specific Dynamic Power ( $\mu\text{W}/\text{MHz}$ )					
		AGLN250	AGLN125	AGLN060	AGLN020	AGLN015	AGLN010
PAC1	Clock contribution of a Global Rib	2.829	2.875	1.728	0	0	0
PAC2	Clock contribution of a Global Spine	1.731	1.265	1.268	2.562	2.562	1.685
PAC3	Clock contribution of a VersaTile row	0.957	0.963	0.967	0.862	0.862	0.858
PAC4	Clock contribution of a VersaTile used as a sequential module	0.098	0.098	0.098	0.094	0.094	0.091
PAC5	First contribution of a VersaTile used as a sequential module	0.045					
PAC6	Second contribution of a VersaTile used as a sequential module	0.186					
PAC7	Contribution of a VersaTile used as a combinatorial module	0.11					
PAC8	Average contribution of a routing net	0.45					
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-13 on page 2-9					
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-14 on page 2-9					
PAC11	Average contribution of a RAM block during a read operation	25.00			N/A		
PAC12	Average contribution of a RAM block during a write operation	30.00			N/A		
PAC13	Dynamic contribution for PLL	2.10			N/A		

**Table 2-18 • Different Components Contributing to the Static Power Consumption in IGLOO nano Devices  
For IGLOO nano V2 Devices, 1.2 V Core Supply Voltage**

Parameter	Definition	Device-Specific Static Power (mW)					
		AGLN250	AGLN125	AGLN060	AGLN020	AGLN015	AGLN010
PDC1	Array static power in Active mode	See Table 2-12 on page 2-8					
PDC2	Array static power in Static (Idle) mode	See Table 2-12 on page 2-8					
PDC3	Array static power in Flash*Freeze mode	See Table 2-9 on page 2-7					
PDC4 <sup>1</sup>	Static PLL contribution	0.90			N/A		
PDC5	Bank quiescent power (VCCI-dependent) <sup>2</sup>	See Table 2-12 on page 2-8					

Notes:

1. Minimum contribution of the PLL when running at lowest frequency.
2. For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or the SmartPower tool in Libero SoC.

**Applies to 1.2 V DC Core Voltage**

**Table 2-43 • 3.3 V LVC MOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage**  
Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.14\text{ V}$ , Worst-Case  $V_{CCI} = 2.7\text{ V}$

Drive Strength	Equivalent Software Default Drive Strength Option <sup>1</sup>	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{PYS}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	Units
100 $\mu\text{A}$	2 mA	STD	1.55	6.01	0.26	1.31	1.91	1.10	6.01	5.66	3.02	3.49	ns
100 $\mu\text{A}$	4 mA	STD	1.55	6.01	0.26	1.31	1.91	1.10	6.01	5.66	3.02	3.49	ns
100 $\mu\text{A}$	6 mA	STD	1.55	5.02	0.26	1.31	1.91	1.10	5.02	4.76	3.38	4.10	ns
100 $\mu\text{A}$	8 mA	STD	1.55	5.02	0.26	1.31	1.91	1.10	5.02	4.76	3.38	4.10	ns

Notes:

1. The minimum drive strength for any LVC MOS 3.3 V software configuration when run in wide range is  $\pm 100\text{ }\mu\text{A}$ . Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

**Table 2-44 • 3.3 V LVC MOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage**  
Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.14\text{ V}$ , Worst-Case  $V_{CCI} = 2.7\text{ V}$

Drive Strength	Equivalent Software Default Drive Strength Option <sup>1</sup>	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{PYS}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	Units
100 $\mu\text{A}$	2 mA	STD	1.55	3.82	0.26	1.31	1.91	1.10	3.82	3.15	3.01	3.65	ns
100 $\mu\text{A}$	4 mA	STD	1.55	3.82	0.26	1.31	1.91	1.10	3.82	3.15	3.01	3.65	ns
100 $\mu\text{A}$	6 mA	STD	1.55	3.25	0.26	1.31	1.91	1.10	3.25	2.61	3.38	4.27	ns
100 $\mu\text{A}$	8 mA	STD	1.55	3.25	0.26	1.31	1.91	1.10	3.25	2.61	3.38	4.27	ns

Notes:

1. The minimum drive strength for any LVC MOS 3.3 V software configuration when run in wide range is  $\pm 100\text{ }\mu\text{A}$ . Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.
3. Software default selection highlighted in gray.

## I/O Register Specifications

### Fully Registered I/O Buffers with Asynchronous Preset

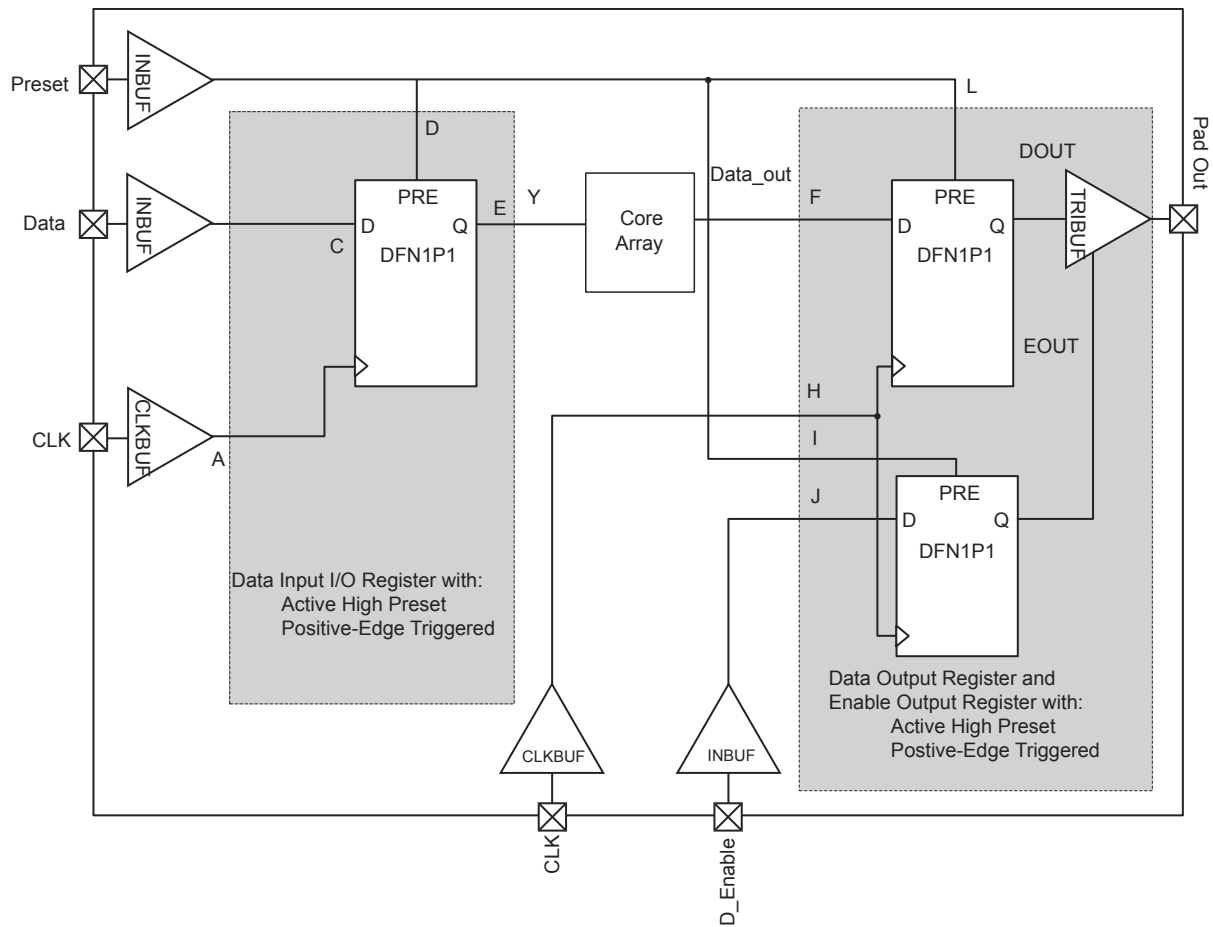
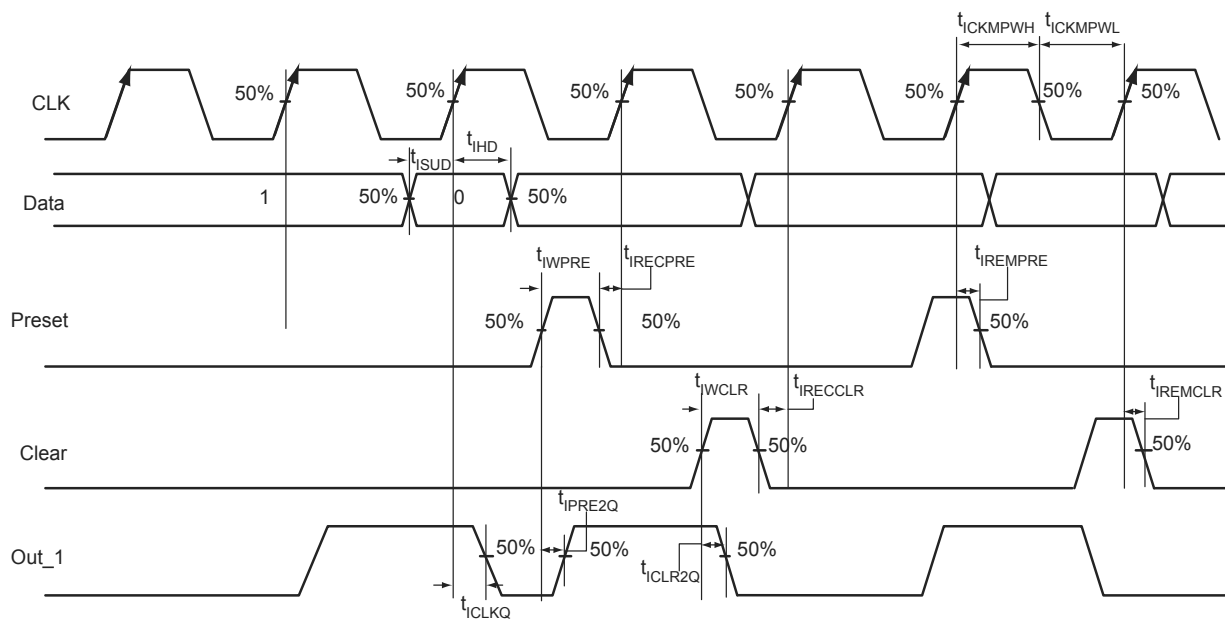


Figure 2-12 • Timing Model of Registered I/O Buffers with Asynchronous Preset



## Input Register



**Figure 2-14 • Input Register Timing Diagram**

### Timing Characteristics

1.5 V DC Core Voltage

**Table 2-72 • Input Data Register Propagation Delays**  
Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
$t_{\text{CLKQ}}$	Clock-to-Q of the Input Data Register	0.42	ns
$t_{\text{ISUD}}$	Data Setup Time for the Input Data Register	0.47	ns
$t_{\text{IHD}}$	Data Hold Time for the Input Data Register	0.00	ns
$t_{\text{ICLR2Q}}$	Asynchronous Clear-to-Q of the Input Data Register	0.79	ns
$t_{\text{IPRE2Q}}$	Asynchronous Preset-to-Q of the Input Data Register	0.79	ns
$t_{\text{IEMCLR}}$	Asynchronous Clear Removal Time for the Input Data Register	0.00	ns
$t_{\text{IRECCLR}}$	Asynchronous Clear Recovery Time for the Input Data Register	0.24	ns
$t_{\text{IEMPRE}}$	Asynchronous Preset Removal Time for the Input Data Register	0.00	ns
$t_{\text{IRECPRE}}$	Asynchronous Preset Recovery Time for the Input Data Register	0.24	ns
$t_{\text{IWCLR}}$	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.19	ns
$t_{\text{IWPRE}}$	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.19	ns
$t_{\text{ICKMPWH}}$	Clock Minimum Pulse Width HIGH for the Input Data Register	0.31	ns
$t_{\text{ICKMPWL}}$	Clock Minimum Pulse Width LOW for the Input Data Register	0.28	ns

*Note:* For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

**Table 2-90 • AGLN020 Global Resource**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.425\text{ V}$**

Parameter	Description	Std.		Units
		Min. <sup>1</sup>	Max. <sup>2</sup>	
$t_{RCKL}$	Input Low Delay for Global Clock	1.21	1.55	ns
$t_{RCKH}$	Input High Delay for Global Clock	1.23	1.65	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
$t_{RCKSW}$	Maximum Skew for Global Clock		0.42	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

**Table 2-91 • AGLN060 Global Resource**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.425\text{ V}$**

Parameter	Description	Std.		Units
		Min. <sup>1</sup>	Max. <sup>2</sup>	
$t_{RCKL}$	Input Low Delay for Global Clock	1.32	1.62	ns
$t_{RCKH}$	Input High Delay for Global Clock	1.34	1.71	ns
$t_{RCKMPWH}$	Minimum Pulse Width HIGH for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width LOW for Global Clock	1.65		ns
$t_{RCKSW}$	Maximum Skew for Global Clock		0.38	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

**Table 2-98 • AGLN125 Global Resource**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.14\text{ V}$**

Parameter	Description	Std.		Units
		Min. <sup>1</sup>	Max. <sup>2</sup>	
$t_{RCKL}$	Input Low Delay for Global Clock	2.08	2.54	ns
$t_{RCKH}$	Input High Delay for Global Clock	2.15	2.77	ns
$t_{RCKMPWH}$	Minimum Pulse Width HIGH for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width LOW for Global Clock	1.65		ns
$t_{RCKSW}$	Maximum Skew for Global Clock		0.62	ns

Notes:

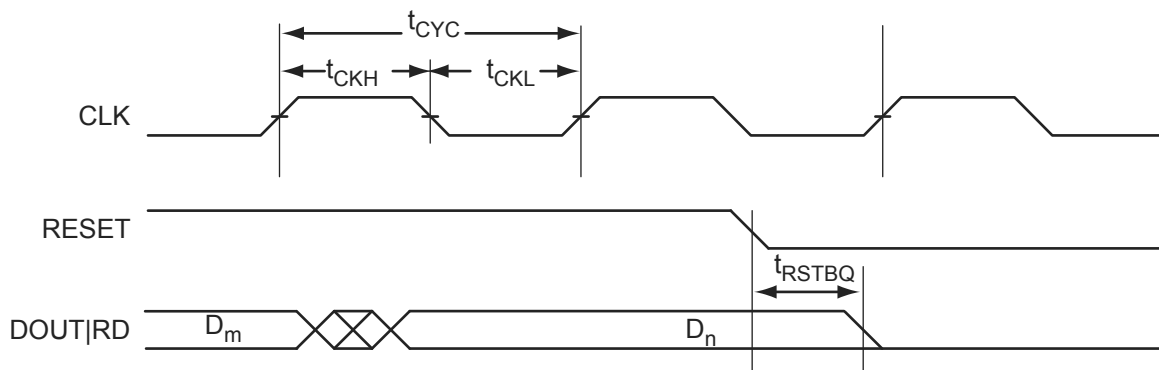
1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

**Table 2-99 • AGLN250 Global Resource**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.14\text{ V}$**

Parameter	Description	Std.		Units
		Min. <sup>1</sup>	Max. <sup>2</sup>	
$t_{RCKL}$	Input Low Delay for Global Clock	2.11	2.57	ns
$t_{RCKH}$	Input High Delay for Global Clock	2.19	2.81	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
$t_{RCKSW}$	Maximum Skew for Global Clock		0.62	ns

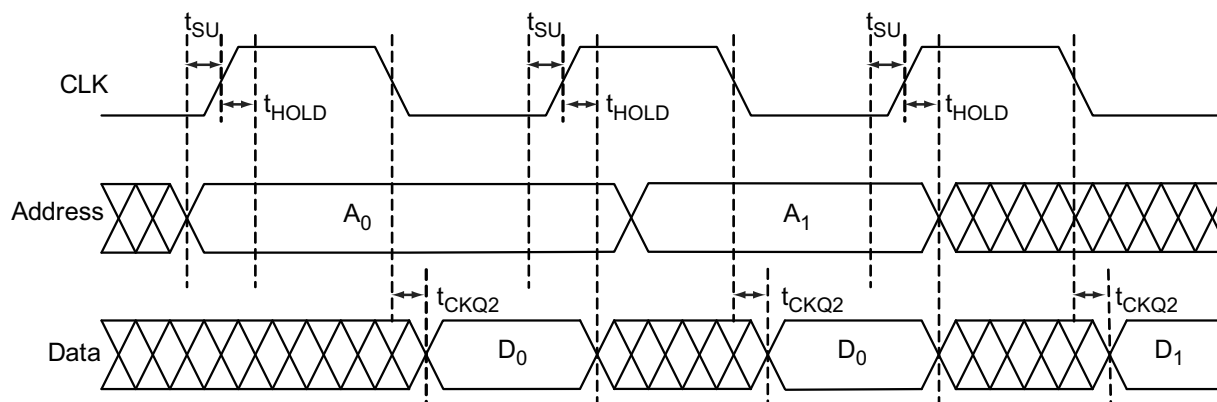
Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.



**Figure 2-32 • RAM Reset. Applicable to Both RAM4K9 and RAM512x18.**

## Embedded FlashROM Characteristics



**Figure 2-41 • Timing Diagram**

### Timing Characteristics

#### 1.5 V DC Core Voltage

**Table 2-108 • Embedded FlashROM Access Time**

Worst Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
$t_{SU}$	Address Setup Time	0.57	ns
$t_{HOLD}$	Address Hold Time	0.00	ns
$t_{CK2Q}$	Clock to Out	20.90	ns
$F_{MAX}$	Maximum Clock Frequency	15	MHz

#### 1.2 V DC Core Voltage

**Table 2-109 • Embedded FlashROM Access Time**

Worst Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.14\text{ V}$

Parameter	Description	Std.	Units
$t_{SU}$	Address Setup Time	0.59	ns
$t_{HOLD}$	Address Hold Time	0.00	ns
$t_{CK2Q}$	Clock to Out	35.74	ns
$F_{MAX}$	Maximum Clock Frequency	10	MHz

should be treated as a sensitive asynchronous signal. When defining pin placement and board layout, simultaneously switching outputs (SSOs) and their effects on sensitive asynchronous pins must be considered.

Unused FF or I/O pins are tristated with weak pull-up. This default configuration applies to both Flash\*Freeze mode and normal operation mode. No user intervention is required.

Table 3-1 shows the Flash\*Freeze pin location on the available packages for IGLOO nano devices. The Flash\*Freeze pin location is independent of device (except for a PQ208 package), allowing migration to larger or smaller IGLOO nano devices while maintaining the same pin location on the board. Refer to the "Flash\*Freeze Technology and Low Power Modes" chapter of the *IGLOO nano FPGA Fabric User's Guide* for more information on I/O states during Flash\*Freeze mode.

**Table 3-1 • Flash\*Freeze Pin Locations for IGLOO nano Devices**

Package	Flash*Freeze Pin
CS81/UC81	H2
QN48	14
QN68	18
VQ100	27
UC36	E2

## JTAG Pins

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the part must be supplied to allow JTAG signals to transition the device. Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

### TCK Test Clock

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pull-up/-down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500  $\Omega$  to 1 k $\Omega$  will satisfy the requirements. Refer to Table 3-2 for more information.

**Table 3-2 • Recommended Tie-Off Values for the TCK and TRST Pins**

VJTAG	Tie-Off Resistance <sup>1,2</sup>
VJTAG at 3.3 V	200 $\Omega$ to 1 k $\Omega$
VJTAG at 2.5 V	200 $\Omega$ to 1 k $\Omega$
VJTAG at 1.8 V	500 $\Omega$ to 1 k $\Omega$
VJTAG at 1.5 V	500 $\Omega$ to 1 k $\Omega$

Notes:

1. The TCK pin can be pulled-up or pulled-down.
2. The TRST pin is pulled-down.
3. Equivalent parallel resistance if more than one device is on the JTAG chain

UC81	
Pin Number	AGLN020 Function
A1	IO64RSB2
A2	IO54RSB2
A3	IO57RSB2
A4	IO36RSB1
A5	IO32RSB1
A6	IO24RSB1
A7	IO20RSB1
A8	IO04RSB0
A9	IO08RSB0
B1	IO59RSB2
B2	IO55RSB2
B3	IO62RSB2
B4	IO34RSB1
B5	IO28RSB1
B6	IO22RSB1
B7	IO18RSB1
B8	IO00RSB0
B9	IO03RSB0
C1	IO51RSB2
C2	IO50RSB2
C3	NC
C4	NC
C5	NC
C6	NC
C7	NC
C8	IO10RSB0
C9	IO07RSB0
D1	IO49RSB2
D2	IO44RSB2
D3	NC
D4	VCC
D5	VCCIB2
D6	GND
D7	NC
D8	IO13RSB0
D9	IO12RSB0

UC81	
Pin Number	AGLN020 Function
E1	GEC0/IO48RSB2
E2	GEA0/IO47RSB2
E3	NC
E4	VCCIB1
E5	VCC
E6	VCCIB0
E7	NC
E8	GDA0/IO15RSB0
E9	GDC0/IO14RSB0
F1	IO46RSB2
F2	IO45RSB2
F3	NC
F4	GND
F5	VCCIB1
F6	NC
F7	NC
F8	IO16RSB0
F9	IO17RSB0
G1	IO43RSB2
G2	IO42RSB2
G3	IO41RSB2
G4	IO31RSB1
G5	NC
G6	IO21RSB1
G7	NC
G8	VJTAG
G9	TRST
H1	IO40RSB2
H2	FF/IO39RSB1
H3	IO35RSB1
H4	IO29RSB1
H5	IO26RSB1
H6	IO25RSB1
H7	IO19RSB1
H8	TDI
H9	TDO

UC81	
Pin Number	AGLN020 Function
J1	IO38RSB1
J2	IO37RSB1
J3	IO33RSB1
J4	IO30RSB1
J5	IO27RSB1
J6	IO23RSB1
J7	TCK
J8	TMS
J9	VPUMP

VQ100	
Pin Number	AGLN030Z Function
1	GND
2	IO82RSB1
3	IO81RSB1
4	IO80RSB1
5	IO79RSB1
6	IO78RSB1
7	IO77RSB1
8	IO76RSB1
9	GND
10	IO75RSB1
11	IO74RSB1
12	GEC0/IO73RSB1
13	GEA0/IO72RSB1
14	GEB0/IO71RSB1
15	IO70RSB1
16	IO69RSB1
17	VCC
18	VCCIB1
19	IO68RSB1
20	IO67RSB1
21	IO66RSB1
22	IO65RSB1
23	IO64RSB1
24	IO63RSB1
25	IO62RSB1
26	IO61RSB1
27	FF/IO60RSB1
28	IO59RSB1
29	IO58RSB1
30	IO57RSB1
31	IO56RSB1
32	IO55RSB1
33	IO54RSB1
34	IO53RSB1
35	IO52RSB1

VQ100	
Pin Number	AGLN030Z Function
36	IO51RSB1
37	VCC
38	GND
39	VCCIB1
40	IO49RSB1
41	IO47RSB1
42	IO46RSB1
43	IO45RSB1
44	IO44RSB1
45	IO43RSB1
46	IO42RSB1
47	TCK
48	TDI
49	TMS
50	NC
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	IO41RSB0
58	IO40RSB0
59	IO39RSB0
60	IO38RSB0
61	IO37RSB0
62	IO36RSB0
63	GDB0/IO34RSB0
64	GDA0/IO33RSB0
65	GDC0/IO32RSB0
66	VCCIB0
67	GND
68	VCC
69	IO31RSB0
70	IO30RSB0

VQ100	
Pin Number	AGLN030Z Function
71	IO29RSB0
72	IO28RSB0
73	IO27RSB0
74	IO26RSB0
75	IO25RSB0
76	IO24RSB0
77	IO23RSB0
78	IO22RSB0
79	IO21RSB0
80	IO20RSB0
81	IO19RSB0
82	IO18RSB0
83	IO17RSB0
84	IO16RSB0
85	IO15RSB0
86	IO14RSB0
87	VCCIB0
88	GND
89	VCC
90	IO12RSB0
91	IO10RSB0
92	IO08RSB0
93	IO07RSB0
94	IO06RSB0
95	IO05RSB0
96	IO04RSB0
97	IO03RSB0
98	IO02RSB0
99	IO01RSB0
100	IO00RSB0



VQ100	
Pin Number	AGLN060 Function
1	GND
2	GAA2/IO51RSB1
3	IO52RSB1
4	GAB2/IO53RSB1
5	IO95RSB1
6	GAC2/IO94RSB1
7	IO93RSB1
8	IO92RSB1
9	GND
10	GFB1/IO87RSB1
11	GFB0/IO86RSB1
12	VCOMPLF
13	GFA0/IO85RSB1
14	VCCPLF
15	GFA1/IO84RSB1
16	GFA2/IO83RSB1
17	VCC
18	VCCIB1
19	GEC1/IO77RSB1
20	GEB1/IO75RSB1
21	GEB0/IO74RSB1
22	GEA1/IO73RSB1
23	GEA0/IO72RSB1
24	VMV1
25	GNDQ
26	GEA2/IO71RSB1
27	FF/GEB2/IO70RSB1
28	GEC2/IO69RSB1
29	IO68RSB1
30	IO67RSB1
31	IO66RSB1
32	IO65RSB1
33	IO64RSB1
34	IO63RSB1
35	IO62RSB1

VQ100	
Pin Number	AGLN060 Function
36	IO61RSB1
37	VCC
38	GND
39	VCCIB1
40	IO60RSB1
41	IO59RSB1
42	IO58RSB1
43	IO57RSB1
44	GDC2/IO56RSB1
45*	GDB2/IO55RSB1
46	GDA2/IO54RSB1
47	TCK
48	TDI
49	TMS
50	VMV1
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO49RSB0
58	GDC0/IO46RSB0
59	GDC1/IO45RSB0
60	GCC2/IO43RSB0
61	GCB2/IO42RSB0
62	GCA0/IO40RSB0
63	GCA1/IO39RSB0
64	GCC0/IO36RSB0
65	GCC1/IO35RSB0
66	VCCIB0
67	GND
68	VCC
69	IO31RSB0
70	GBC2/IO29RSB0

VQ100	
Pin Number	AGLN060 Function
71	GBB2/IO27RSB0
72	IO26RSB0
73	GBA2/IO25RSB0
74	VMV0
75	GNDQ
76	GBA1/IO24RSB0
77	GBA0/IO23RSB0
78	GBB1/IO22RSB0
79	GBB0/IO21RSB0
80	GBC1/IO20RSB0
81	GBC0/IO19RSB0
82	IO18RSB0
83	IO17RSB0
84	IO15RSB0
85	IO13RSB0
86	IO11RSB0
87	VCCIB0
88	GND
89	VCC
90	IO10RSB0
91	IO09RSB0
92	IO08RSB0
93	GAC1/IO07RSB0
94	GAC0/IO06RSB0
95	GAB1/IO05RSB0
96	GAB0/IO04RSB0
97	GAA1/IO03RSB0
98	GAA0/IO02RSB0
99	IO01RSB0
100	IO00RSB0

Note: \*The bus hold attribute (hold previous I/O state in Flash\*Freeze mode) is not supported for pin 45 in AGLN060-VQ100.

VQ100	
Pin Number	AGLN125 Function
1	GND
2	GAA2/IO67RSB1
3	IO68RSB1
4	GAB2/IO69RSB1
5	IO132RSB1
6	GAC2/IO131RSB1
7	IO130RSB1
8	IO129RSB1
9	GND
10	GFB1/IO124RSB1
11	GFB0/IO123RSB1
12	VCOMPLF
13	GFA0/IO122RSB1
14	VCCPLF
15	GFA1/IO121RSB1
16	GFA2/IO120RSB1
17	VCC
18	VCCIB1
19	GEC0/IO111RSB1
20	GEB1/IO110RSB1
21	GEB0/IO109RSB1
22	GEA1/IO108RSB1
23	GEA0/IO107RSB1
24	VMV1
25	GNDQ
26	GEA2/IO106RSB1
27	FF/GEB2/IO105RSB1
28	GEC2/IO104RSB1
29	IO102RSB1
30	IO100RSB1
31	IO99RSB1
32	IO97RSB1
33	IO96RSB1
34	IO95RSB1
35	IO94RSB1
36	IO93RSB1

VQ100	
Pin Number	AGLN125 Function
37	VCC
38	GND
39	VCCIB1
40	IO87RSB1
41	IO84RSB1
42	IO81RSB1
43	IO75RSB1
44	GDC2/IO72RSB1
45	GDB2/IO71RSB1
46	GDA2/IO70RSB1
47	TCK
48	TDI
49	TMS
50	VMV1
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO65RSB0
58	GDC0/IO62RSB0
59	GDC1/IO61RSB0
60	GCC2/IO59RSB0
61	GCB2/IO58RSB0
62	GCA0/IO56RSB0
63	GCA1/IO55RSB0
64	GCC0/IO52RSB0
65	GCC1/IO51RSB0
66	VCCIB0
67	GND
68	VCC
69	IO47RSB0
70	GBC2/IO45RSB0
71	GBB2/IO43RSB0
72	IO42RSB0

VQ100	
Pin Number	AGLN125 Function
73	GBA2/IO41RSB0
74	VMV0
75	GNDQ
76	GBA1/IO40RSB0
77	GBA0/IO39RSB0
78	GBB1/IO38RSB0
79	GBB0/IO37RSB0
80	GBC1/IO36RSB0
81	GBC0/IO35RSB0
82	IO32RSB0
83	IO28RSB0
84	IO25RSB0
85	IO22RSB0
86	IO19RSB0
87	VCCIB0
88	GND
89	VCC
90	IO15RSB0
91	IO13RSB0
92	IO11RSB0
93	IO09RSB0
94	IO07RSB0
95	GAC1/IO05RSB0
96	GAC0/IO04RSB0
97	GAB1/IO03RSB0
98	GAB0/IO02RSB0
99	GAA1/IO01RSB0
100	GAA0/IO00RSB0

Revision	Changes	Page
Revision 11 (Jul 2010)	The status of the AGLN060 device has changed from Advance to Production.	III
	The values for PAC1, PAC2, PAC3, and PAC4 were updated in Table 2-15 • Different Components Contributing to Dynamic Power Consumption in IGLOO nano Devices for 1.5 V core supply voltage (SAR 26404).	2-10
	The values for PAC1, PAC2, PAC3, and PAC4 were updated in Table 2-17 • Different Components Contributing to Dynamic Power Consumption in IGLOO nano Devices for 1.2 V core supply voltage (SAR 26404).	2-11
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "IGLOO nano Device Status" table on page III indicates the status for each device in the device family.	N/A
Revision 10 (Apr 2010)	References to differential inputs were removed from the datasheet, since IGLOO nano devices do not support differential inputs (SAR 21449).	N/A
	A parenthetical note, "hold previous I/O state in Flash*Freeze mode," was added to each occurrence of bus hold in the datasheet (SAR 24079).	N/A
	The "In-System Programming (ISP) and Security" section was revised to add 1.2 V programming.	I
	The note connected with the "IGLOO nano Ordering Information" table was revised to clarify features not available for Z feature grade devices.	IV
	The "IGLOO nano Device Status" table is new.	III
	The definition of C in the "Temperature Grade Offerings" table was changed to "extended commercial temperature range".	VI
	1.2 V wide range was added to the list of voltage ranges in the "I/Os with Advanced I/O Standards" section.	1-8
	A note was added to Table 2-2 • Recommended Operating Conditions <sup>1</sup> regarding switching from 1.2 V to 1.5 V core voltage for in-system programming. The VJTAG voltage was changed from "1.425 to 3.6" to "1.4 to 3.6" (SAR 24052). The note regarding voltage for programming V2 and V5 devices was revised (SAR 25213). The maximum value for VPUMP programming voltage (operation mode) was changed from 3.45 V to 3.6 V (SAR 25220).	2-2
	Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.425 V) and Table 2-7 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.14 V) were updated. Table 2-8 • Power Supply State per Mode is new.	2-6, 2-7
	The tables in the "Quiescent Supply Current" section were updated (SAR 24882 and SAR 24112).	2-7
	VJTAG was removed from Table 2-10 • Quiescent Supply Current (IDD) Characteristics, IGLOO nano Sleep Mode* (SARs 24112, 24882, and 79503).	2-8
	The note stating what was included in I <sub>DD</sub> was removed from Table 2-11 • Quiescent Supply Current (IDD) Characteristics, IGLOO nano Shutdown Mode. The note, "per VCCI or VJTAG bank" was removed from Table 2-12 • Quiescent Supply Current (IDD), No IGLOO nano Flash*Freeze Mode <sup>1</sup> . The note giving I <sub>DD</sub> was changed to "I <sub>DD</sub> = N <sub>BANKS</sub> * I <sub>CCI</sub> + I <sub>CCA</sub> ".	2-8
	The values in Table 2-13 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings and Table 2-14 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings <sup>1</sup> were updated. Wide range support information was added.	2-9

Revision / Version	Changes	Page
<b>Revision 9 (Mar2010)</b> Product Brief Advance v0.9 Packaging Advance v0.8	All product tables and pin tables were updated to show clearly that AGLN030 is available only in the Z feature grade at this time. The nano-Z feature grade devices are designated with a Z at the end of the part number.	N/A
<b>Revision 8 (Jan 2009)</b>  Product Brief Advance v0.8	The "Reprogrammable Flash Technology" section was revised to add "250 MHz (1.5 V systems) and 160 MHz (1.2 V systems) System Performance".	I
	The note for AGLN030 in the "IGLOO nano Devices" table and "I/Os Per Package" table was revised to remove the statement regarding package compatibility with lower density nano devices.	II, II
	The "I/Os with Advanced I/O Standards" section was revised to add definitions for hot-swap and cold-sparing.	1-8
Packaging Advance v0.7	The "UC81", "CS81", "QN48", and "QN68" pin tables for AGLN030 are new.	4-5, 4-8, 4-17, 4-21
	The "CS81" pin table for AGLN060 is new.	4-9
	The "CS81" and "VQ100" pin tables for AGLN060Z are new.	4-10, 4-25
	The "CS81" and "VQ100" pin tables for AGLN125Z are new.	4-12, 4-27
	The "CS81" and "VQ100" pin tables for AGLN250Z are new.	4-14, 4-29
<b>Revision 7 (Apr 2009)</b> Product Brief Advance v0.7 DC and Switching Characteristics Advance v0.3	The –F speed grade is no longer offered for IGLOO nano devices and was removed from the datasheet.	N/A
<b>Revision 6 (Mar 2009)</b> Packaging Advance v0.6	The "VQ100" pin table for AGLN030 is new.	4-23
<b>Revision 5 (Feb 2009)</b> Packaging Advance v0.5	The "100-Pin QFN" section was removed.	N/A
<b>Revision 4 (Feb 2009)</b>  Product Brief Advance v0.6	The QN100 package was removed for all devices.	N/A
	"IGLOO nano Devices" table was updated to change the maximum user I/Os for AGLN030 from 81 to 77.	II
	The "Device Marking" section is new.	V
<b>Revision 3 (Feb 2009)</b> Product Brief Advance v0.5	The following table note was removed from "IGLOO nano Devices" table: "Six chip (main) and three quadrant global networks are available for AGLN060 and above."	II
	The CS81 package was added for AGLN250 in the "IGLOO nano Products Available in the Z Feature Grade" table.	VI
Packaging Advance v0.4	The "UC81" and "CS81" pin tables for AGLN020 are new.	4-4, 4-7
	The "CS81" pin table for AGLN250 is new.	4-13



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